
HSM109WK

Silicon Schottky Barrier Diode for Battery Switch

HITACHI

ADE-208-059C(Z)

Rev 3

September 1996

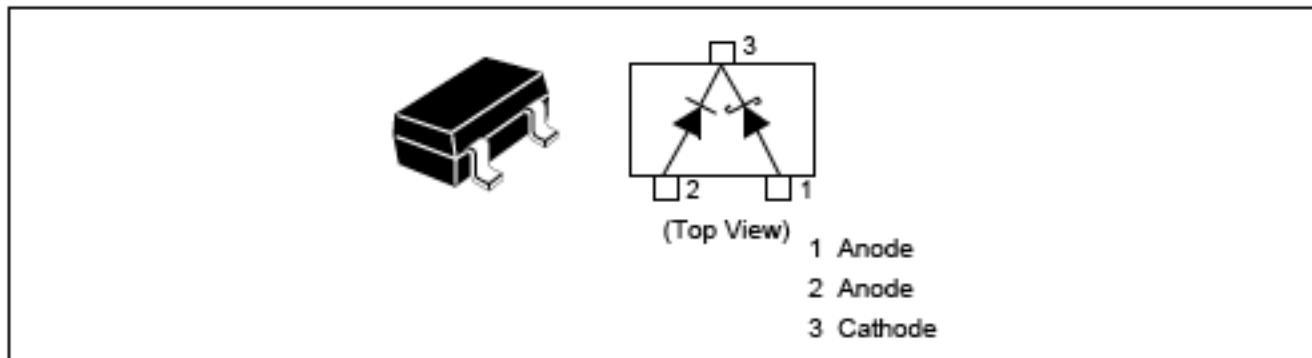
Features

- The HSM109WK has two different (VF- IF) chips, and can change the main battery to the backup battery automatically.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSM109WK	S7	MPAK

Outline



HSM109WK

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value (Pin1-3)	Value (Pin2-3)	Unit
Peak reverse voltage	VRM	10	10	V
Forward current	IF	30	30	mA
Junction temperature	Tj	125	125	°C
Storage temperature	Tstg	-55 to +125	-55 to +125	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol		Min	Typ	Max	Unit	Test Condition
Forward voltage	VF	Pin 1-3	0.1	0.1	0.3	V	IF = 1 mA
		Pin 2-3	0.5	0.5	0.8		
Reverse current	IR	Pin 1-3	0.1	0.1	5.0	μA	VR = 5V
		Pin 2-3	0.1	0.1	0.1		
ESD-Capability	ESD		225	225	225	V	C=200pF, RL=100Ω, Both forward and reverse direction 5 pulse.

Main Characteristic

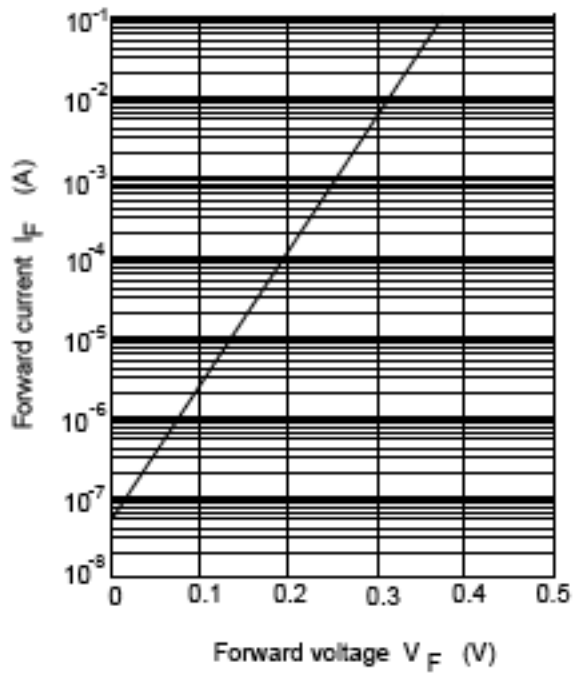


Fig.1 Forward current Vs. Forward voltage (Pin 1 - 3)

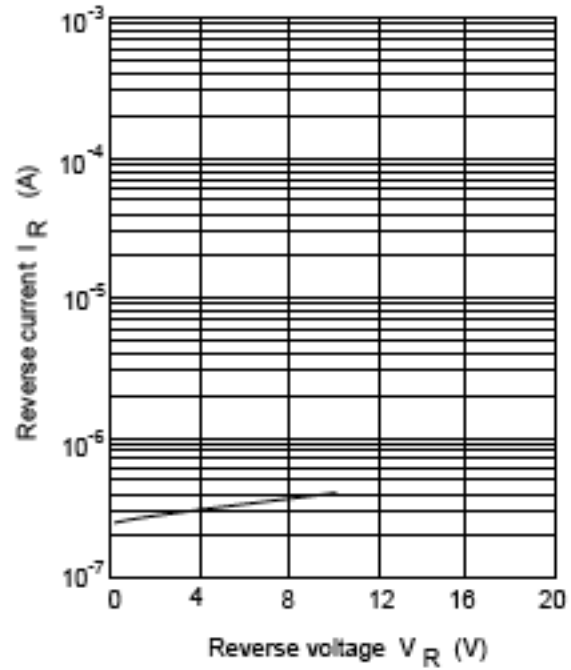


Fig.2 Reverse current Vs. Reverse voltage (Pin 1 - 3)

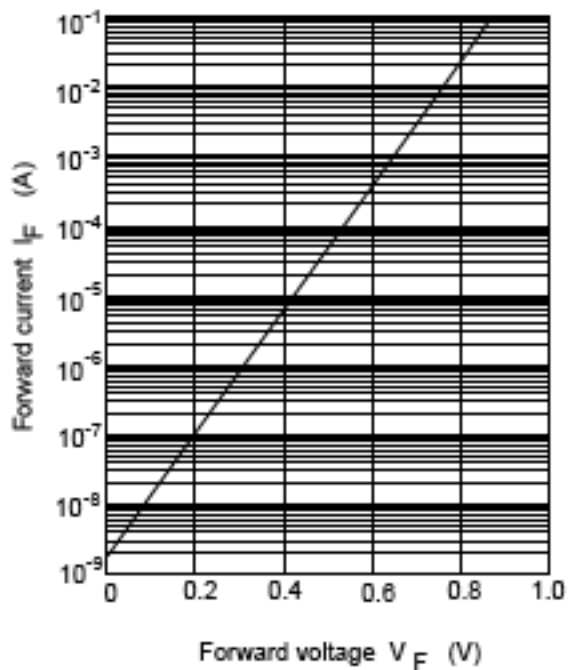


Fig.3 Forward current Vs. Forward voltage (Pin 2 - 3)

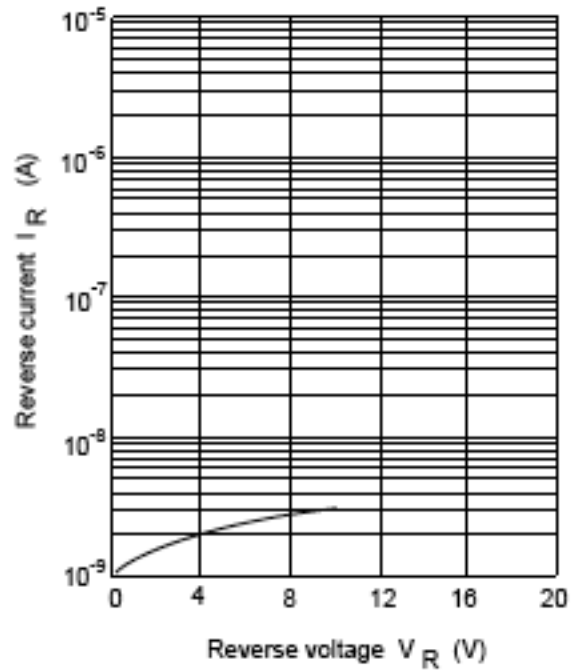


Fig.4 Reverse current Vs. Reverse voltage (Pin 2 - 3)

Main Characteristic

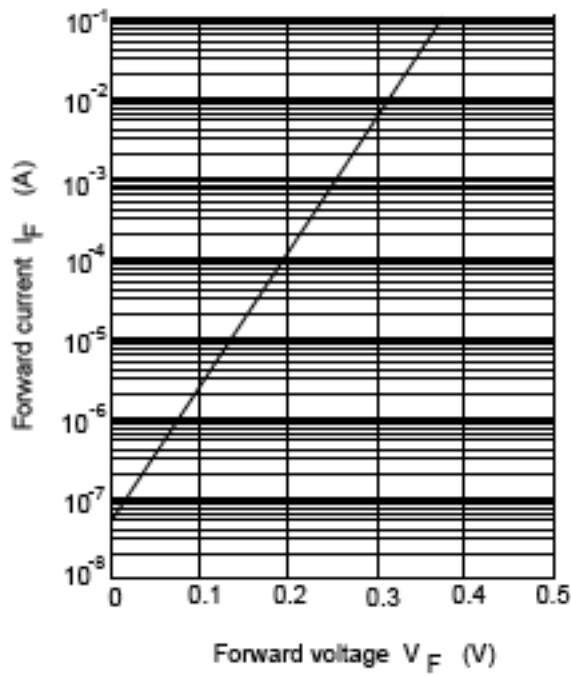


Fig.1 Forward current Vs. Forward voltage (Pin 1 - 3)

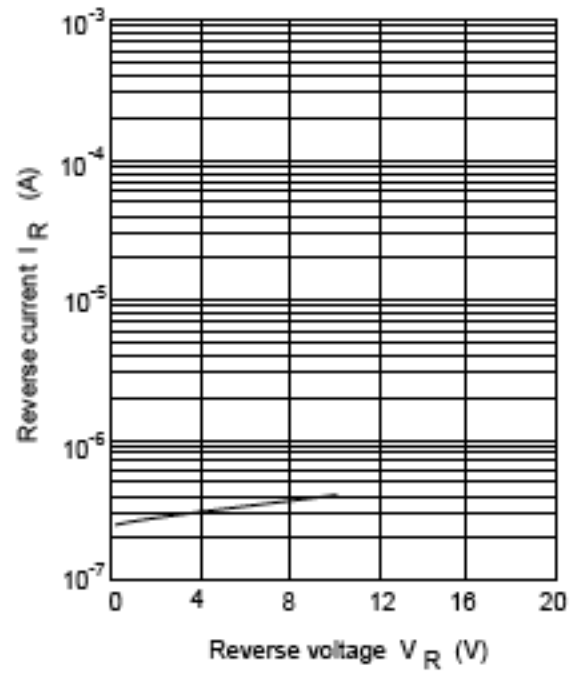


Fig.2 Reverse current Vs. Reverse voltage (Pin 1 - 3)

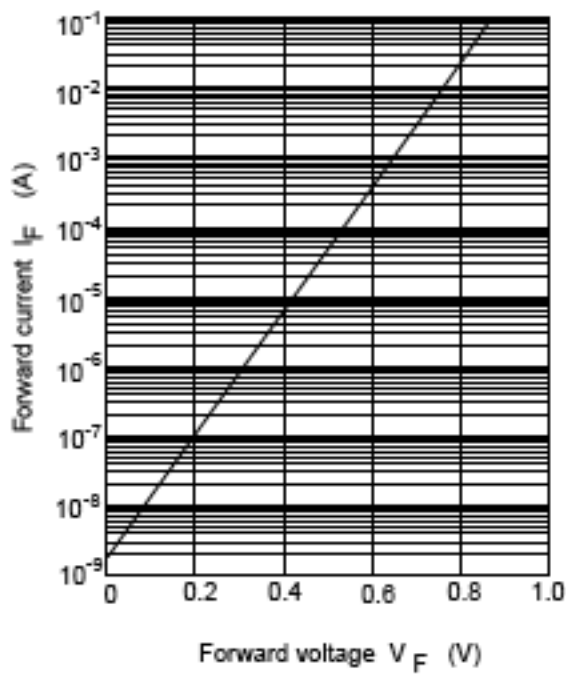


Fig.3 Forward current Vs. Forward voltage (Pin 2 - 3)

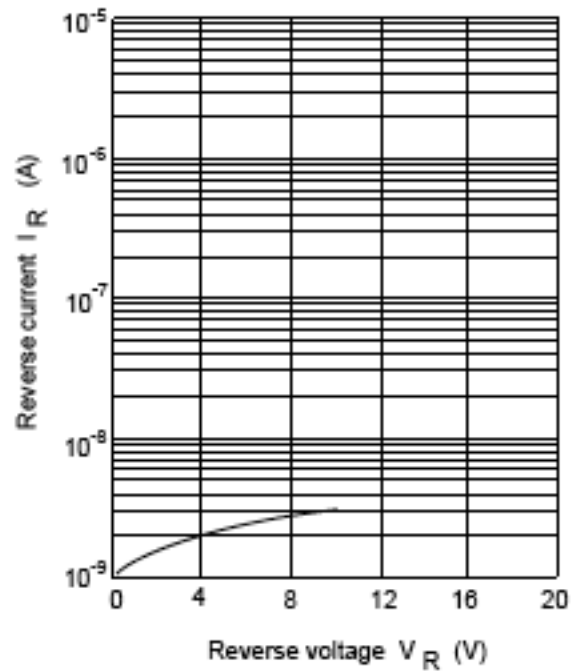


Fig.4 Reverse current Vs. Reverse voltage (Pin 2 - 3)